

N-channel 80 V 8.7 mΩ standard level MOSFET in TO-220 Rev. 02 — 1 November 2010 Product data

Product data sheet

#### **Product profile** 1.

#### **1.1 General description**

Standard level N-channel MOSFET in TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive

#### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

#### 1.4 Quick reference data

#### Table 1. **Quick reference data**

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	80	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V};$ see <u>Figure 1</u>		-	-	90	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see Figure 2		-	-	170	W
Tj	junction temperature			-55	-	175	°C
Static char	racteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 10 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } Figure 12$		-	-	14	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	<u>[1]</u>	-	7.5	8.7	mΩ
Dynamic o	characteristics						
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; $I_{D}$ = 25 A;		-	11	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 40 V; see <u>Figure 14</u> ; see <u>Figure 15</u>		-	52	-	nC
Avalanche	ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy			-	-	120	mJ

[1] Measured 3 mm from package.

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#### N-channel 80 V 8.7 m $\Omega$ standard level MOSFET in TO-220

### 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT78 (TO-220AB)	

### 3. Ordering information

#### Table 3.Ordering information

Type number	Package					
	Name	Description	Version			
PSMN8R7-80PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

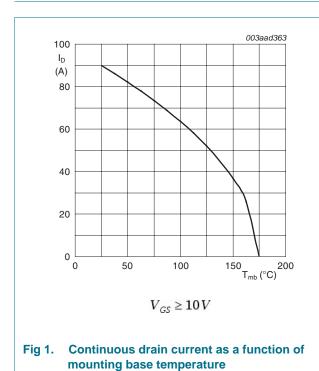
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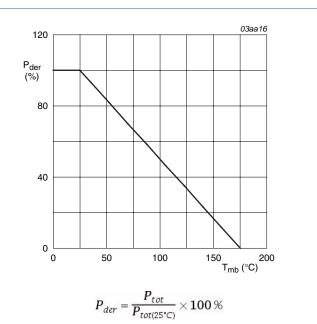
### 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	80	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	80	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; see <u>Figure 1</u>	-	64	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	-	90	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	361	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	170	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-drain	diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	90	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	361	А
Avalanche rug	ggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 90 A; $V_{sup} \le 80$ V; $R_{GS}$ = 50 $\Omega$ ; unclamped	-	120	mJ

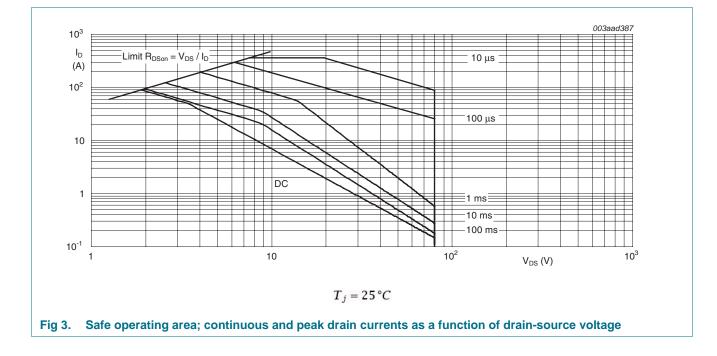






# PSMN8R7-80PS

#### N-channel 80 V 8.7 m $\Omega$ standard level MOSFET in TO-220



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Р

Ηm

10<sup>-1</sup>

t<sub>p</sub> |-

т

t<sub>p</sub> (s)

 $\delta = \frac{t_p}{T}$ 

t

1

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### 5. Thermal characteristics

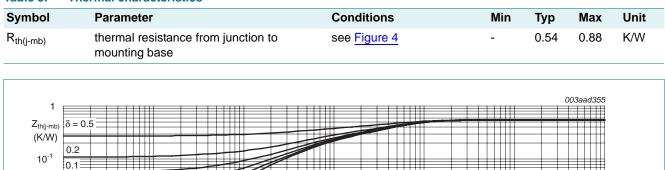
Ш

Π

10-5

single shot

10-4



++++

10<sup>-2</sup>

#### Table 5. Thermal characteristics

0.05

0.02

10<sup>-2</sup>

10<sup>-3</sup>

10<sup>-4</sup>

10<sup>-6</sup>

Fig 4. Transien values	t thermal impedance from junction to mounting base as a function of pulse duration; typical
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10<sup>-3</sup>

N-channel 80 V 8.7 m $\Omega$  standard level MOSFET in TO-220

### 6. Characteristics

#### Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	73	-	-	V
		$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	80	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <u>Figure 10</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 10	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 10</u>	2.3	3	4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.3	5	μΑ
		$V_{DS} = 80 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ T}_{j} = 125 \text{ °C}$	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
		$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	10	100	nA
R <sub>DSon</sub> drain-sour	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 175 °C; see <u>Figure 12</u>		20.8 8	mΩ	
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 100 °C; see <u>Figure 12</u>	-	-	14	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 10 A; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	<u>[1]</u> -	7.5	8.7	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	1	-	Ω
Dynamic o	haracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	44	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	52	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 14; see Figure 15	-	15	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	9.2	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge	see Figure 14	-	5.8	-	nC
Q <sub>GD</sub>	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	11	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; \text{ see } \frac{\text{Figure } 15}{100000000000000000000000000000000000$	-	4.6	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 40 V; V_{GS} = 0 V; f = 1 MHz;$	-	3346	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 16$	-	296	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	158	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 40 V; $R_{L}$ = 1.6 $\Omega$ ; $V_{GS}$ = 10 V;	-	21	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	26	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	46	-	ns
t <sub>f</sub>	fall time		-	20	-	ns
Source-dra	ain diode					
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 10 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 17</u>	-	0.79	1.2	V

003aad451

T<sub>j</sub> = 25 °C

V<sub>GS</sub> (V)

003aad456

80 <sub>I<sub>D</sub> (A)</sub> 100

6

4

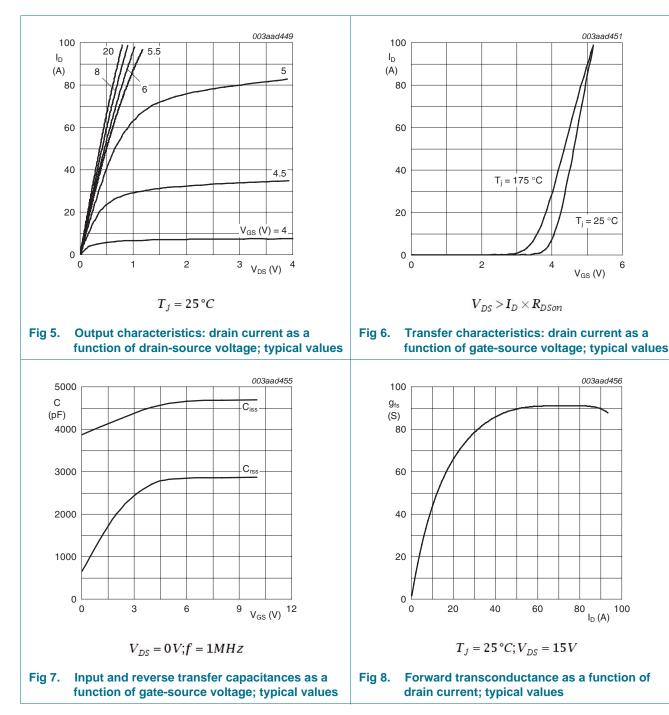
#### N-channel 80 V 8.7 mΩ standard level MOSFET in TO-220

#### Characteristics ... continued Table 6.

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = 100 \text{ A}/\mu\text{s};$	-	42	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_{DS} = 40 V$	-	66	-	nC

[1] Measured 3 mm from package.

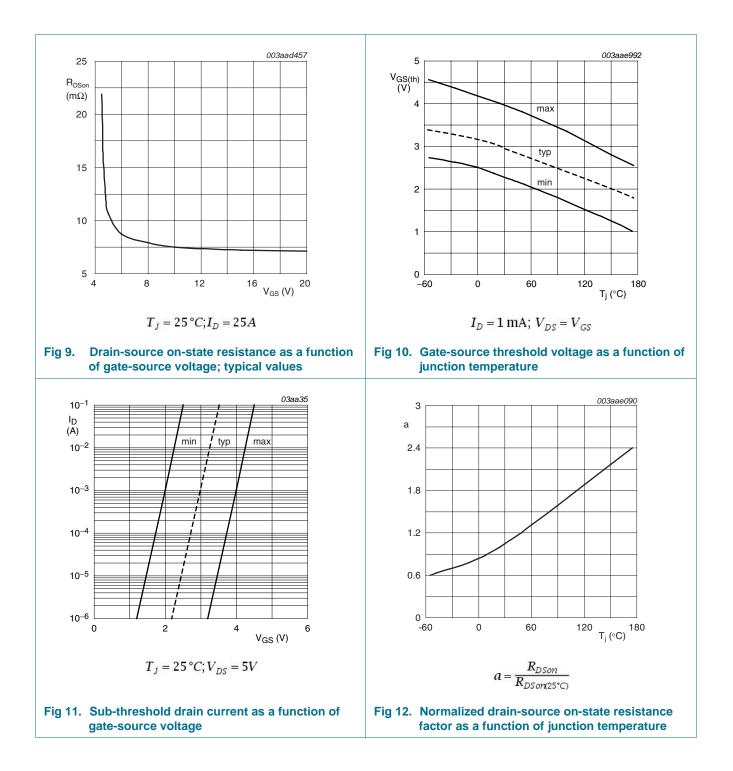


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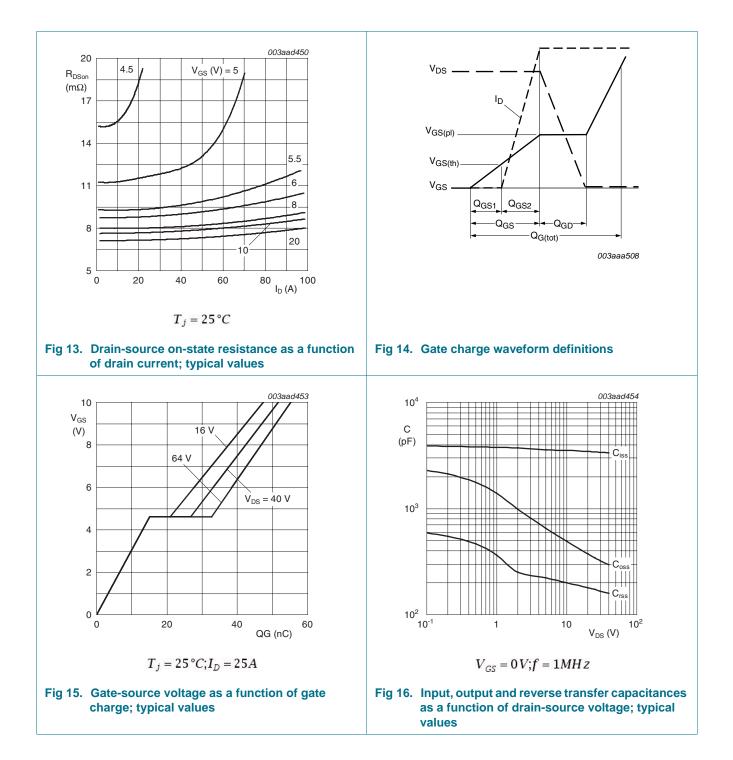
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#### N-channel 80 V 8.7 mΩ standard level MOSFET in TO-220



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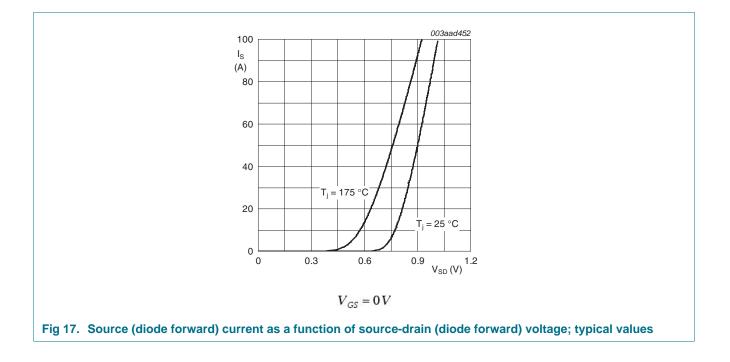
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# PSMN8R7-80PS

#### N-channel 80 V 8.7 m $\Omega$ standard level MOSFET in TO-220



#### N-channel 80 V 8.7 mΩ standard level MOSFET in TO-220

#### **Package outline** 7.

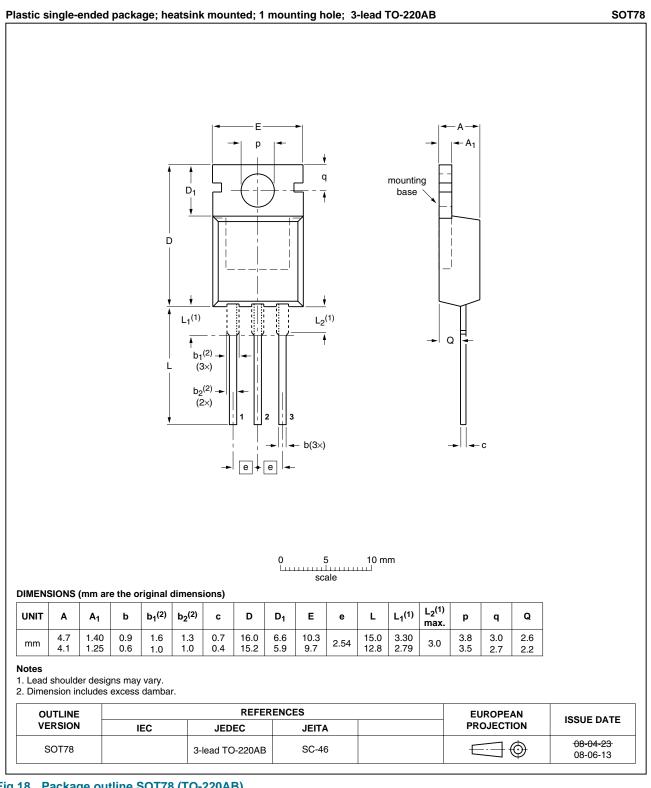


Fig 18. Package outline SOT78 (TO-220AB)

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### 8. Revision history

Table 7.Revision h	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN8R7-80PS v.2	20101101	Product data sheet	-	PSMN8R7-80PS v.1
Modifications:	<ul> <li>Status change</li> </ul>	ed from objective to product.		
	<ul> <li>Various chang</li> </ul>	es to content.		
PSMN8R7-80PS v.1	20100129	Objective data sheet	-	-

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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